BT137 series D

GENERAL DESCRIPTION

Glass passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate

QUICK REFERENCE DATA

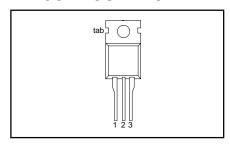
SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BT137- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500D 500 8 65	600D 600 8 65	V A A

PINNING - TO220AB

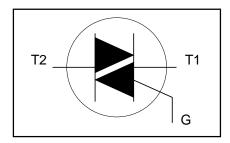
trigger circuits.

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS MIN. MAX.		۸X.	UNIT	
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	V
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge	-	8		A
		t = 20 ms t = 16.7 ms	-	6 7		A A
l ² t dl _T /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 10.7 ms t = 10 ms $I_{TM} = 12 \text{ A}; I_{G} = 0.2 \text{ A};$ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-	2		A A ² s
	triggering	T2+ G+ T2+ G- T2- G- T2- G+	- - -	5 5 5	0	A/μs A/μs A/μs A/μs
I _{GM} V _{GM} P _{GM}	Peak gate current Peak gate voltage Peak gate power	12-04	- - -	2	2	Αμ3 Α V W
P _{G(AV)} T _{stg}	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- -40 -	0. 15	.5 50 25	°C °C

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/µs.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	1 1 1	- - 60	2.0 2.4 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
			2+ G+	-	2.5	5	mΑ
		T	2+ G-	-	3.5	5 5	mΑ
			⁻ 2- G-	-	3.5		mΑ
			⁻ 2- G+	-	6.5	10	mΑ
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
			T2+ G+	-	1.6	15	mΑ
		-	⁻ 2+ G-	-	8.5	20	mΑ
			2- G-	-	1.2	15	mΑ
		-	⁻ 2- G+	-	2.5	20	mA
l I _H	Holding current	$V_D = 12 V; I_{GT} = 0.1 A$		-	1.5	10	mΑ
V _T	On-state voltage	$I_{T} = 10 \text{ A}$		-	1.3	1.65	V
V _{GT}	Gate trigger voltage	$\begin{vmatrix} \dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A} \\ V_{D} = 400 \text{ V}; I_{T} = 0.1 \text{ A}; T_{i} = 125 ^{\circ}\text{C}$	_	-	0.7	1.5	V
	l	$ V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$)	0.25	0.4		V
I_{D}	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125$ °C		-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	-	5	-	V/μs
$\mathbf{t}_{ ext{gt}}$	off-state voltage Gate controlled turn-on time	exponential waveform; $R_{GK} = 1 \text{ k}\Omega$ $I_{TM} = 12 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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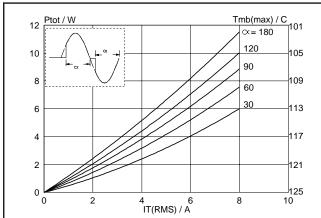


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

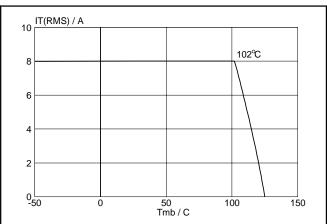


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

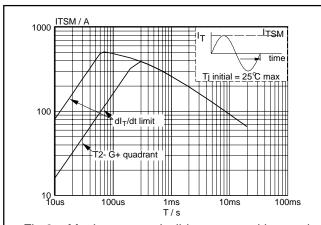


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

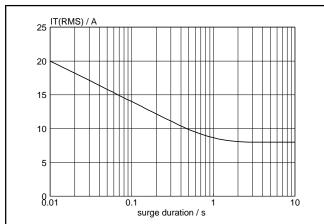


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 102$ °C.

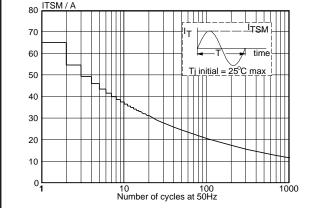


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

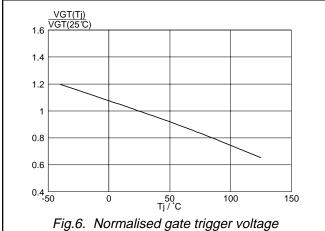
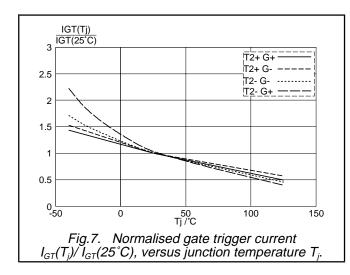
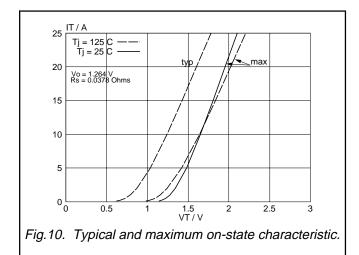
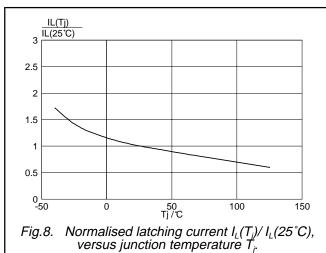


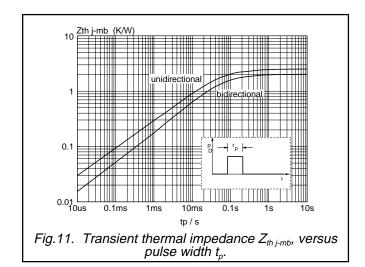
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_j .

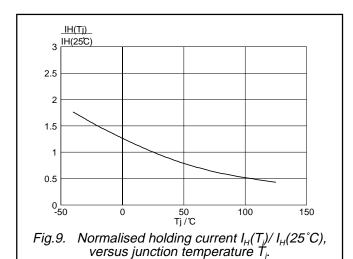
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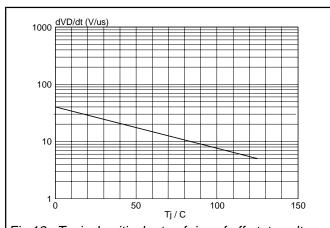
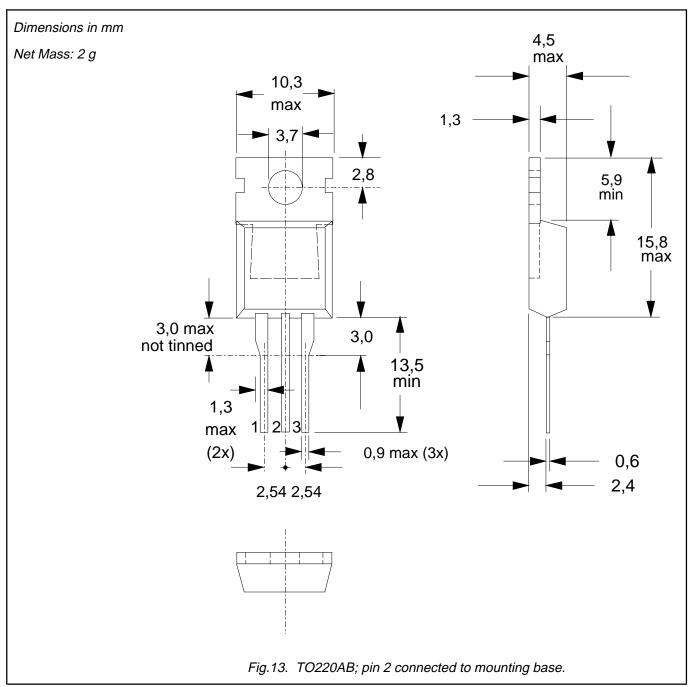


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j.

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MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for TO220 envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Triacs logic level

BT137 series D

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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